

# High Speed, High Gain Bipolar NPN Power Transistor

with Integrated Collector-Emitter  
Diode and Built-in Efficient  
Antisaturation Network

## BUL45D2G

The BUL45D2G is state-of-art High Speed High gain BiPolar transistor (H2BIP). High dynamic characteristics and lot-to-lot minimum spread ( $\pm 150$  ns on storage time) make it ideally suitable for light ballast applications. Therefore, there is no need to guarantee an  $h_{FE}$  window. It's characteristics make it also suitable for PFC application.

### Features

- Low Base Drive Requirement
- High Peak DC Current Gain
- Extremely Low Storage Time Min/Max Guarantees Due to the H2BIP Structure which Minimizes the Spread
- Integrated Collector-Emitter Free Wheeling Diode
- Fully Characterized and Guaranteed Dynamic  $V_{CE(sat)}$
- "6 Sigma" Process Providing Tight and Reproducible Parameter Spreads
- These Devices are Pb-Free and are RoHS Compliant\*

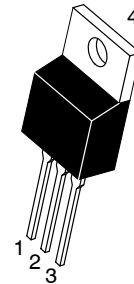
### MAXIMUM RATINGS

Symbol	Rating	Value	Unit
$V_{CEO}$	Collector-Emitter Sustaining Voltage	400	Vdc
$V_{CBO}$	Collector-Base Breakdown Voltage	700	Vdc
$V_{CES}$	Collector-Emitter Breakdown Voltage	700	Vdc
$V_{EBO}$	Emitter-Base Voltage	12	Vdc
$I_C$	Collector Current - Continuous	5	Adc
$I_{CM}$	Collector Current - Peak (Note 1)	10	Adc
$I_B$	Base Current - Continuous	2	Adc
$I_{BM}$	Base Current - Peak (Note 1)	4	Adc
$P_D$	Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	75 0.6	W W/ $^\circ\text{C}$
$T_J, T_{stg}$	Operating and Storage Temperature	-65 to +150	$^\circ\text{C}$

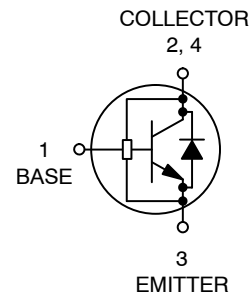
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq 10\%$ .

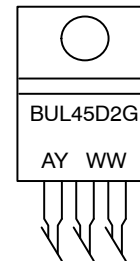
POWER TRANSISTOR  
5.0 AMPERES,  
700 VOLTS, 75 WATTS



TO-220  
CASE 221A  
STYLE 1



### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
BUL45D2G	TO-220 (Pb-Free)	50 Units / Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the [onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

# BUL45D2G

## THERMAL CHARACTERISTICS

Symbol	Characteristics	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.65	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^{\circ}\text{C}/\text{W}$
$T_L$	Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	260	$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage ( $I_C = 100\text{ mA}$ , $L = 25\text{ mH}$ )	400	450	–	Vdc
$V_{CBO}$	Collector-Base Breakdown Voltage ( $I_{CBO} = 1\text{ mA}$ )	700	910	–	Vdc
$V_{EBO}$	Emitter-Base Breakdown Voltage ( $I_{EBO} = 1\text{ mA}$ )	12	14.1	–	Vdc
$I_{CEO}$	Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CEO}$ , $I_B = 0$ )	–	–	100	$\mu\text{Adc}$
$I_{CES}$	Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CES}$ , $V_{EB} = 0$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $V_{CE} = 500\text{ V}$ , $V_{EB} = 0$ ) @ $T_C = 125^{\circ}\text{C}$	– – –	– – –	100 500 100	$\mu\text{Adc}$
$I_{EBO}$	Emitter-Cutoff Current ( $V_{EB} = 10\text{ Vdc}$ , $I_C = 0$ )	–	–	100	$\mu\text{Adc}$

### ON CHARACTERISTICS

$V_{BE(sat)}$	Base-Emitter Saturation Voltage ( $I_C = 0.8\text{ Adc}$ , $I_B = 80\text{ mAdc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $I_C = 2\text{ Adc}$ , $I_B = 0.4\text{ Adc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	– – – –	0.8 0.7 0.89 0.79	1 0.9 1 0.9	Vdc
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C = 0.8\text{ Adc}$ , $I_B = 80\text{ mAdc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $I_C = 2\text{ Adc}$ , $I_B = 0.4\text{ Adc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $I_C = 0.8\text{ Adc}$ , $I_B = 40\text{ mAdc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	– – – – – –	0.28 0.32 0.32 0.38 0.46 0.62	0.4 0.5 0.5 0.6 0.75 1	Vdc
$h_{FE}$	DC Current Gain ( $I_C = 0.8\text{ Adc}$ , $V_{CE} = 1\text{ Vdc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $I_C = 2\text{ Adc}$ , $V_{CE} = 1\text{ Vdc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	22 20 10 7	34 29 14 9.5	– – – –	–

### DIODE CHARACTERISTICS

$V_{EC}$	Forward Diode Voltage ( $I_{EC} = 1\text{ Adc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $I_{EC} = 2\text{ Adc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$ ( $I_{EC} = 0.4\text{ Adc}$ ) @ $T_C = 25^{\circ}\text{C}$ @ $T_C = 125^{\circ}\text{C}$	– – – – – –	1.04 0.7 1.2 – 0.85 0.62	1.5 – 1.6 – 1.2 –	V
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# BUL45D2G

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted) (continued)

Symbol	Characteristic	Min	Typ	Max	Unit
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### DIODE CHARACTERISTICS

T <sub>fr</sub>	Forward Recovery Time (see Figure 27)				ns
	(I <sub>F</sub> = 1 Adc, di/dt = 10 A/μs)				
	@ T <sub>C</sub> = 25°C	–	330	–	
	(I <sub>F</sub> = 2 Adc, di/dt = 10 A/μs)				
	@ T <sub>C</sub> = 25°C	–	360	–	
	(I <sub>F</sub> = 0.4 Adc, di/dt = 10 A/μs)				
	@ T <sub>C</sub> = 25°C	–	320	–	

### DYNAMIC CHARACTERISTICS

f <sub>T</sub>	Current Gain Bandwidth (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1 MHz)	–	13	–	MHz
C <sub>ob</sub>	Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1 MHz)	–	50	75	pF
C <sub>ib</sub>	Input Capacitance (V <sub>EB</sub> = 8 Vdc)	–	340	500	pF

### DYNAMIC SATURATION VOLTAGE

V <sub>CE(dsat)</sub>	Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I <sub>B1</sub> reaches 90% of final I <sub>B1</sub>	I <sub>C</sub> = 1 A I <sub>B1</sub> = 100 mA V <sub>CC</sub> = 300 V	@ 1 μs	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	3.7 9.4	– –	V
			@ 3 μs	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	0.35 2.7	– –	V
		I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.8 A V <sub>CC</sub> = 300 V	@ 1 μs	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	3.9 12	– –	V
			@ 3 μs	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	0.4 1.5	– –	V

### SWITCHING CHARACTERISTICS: Resistive Load (D.C. ≤ 10%, Pulse Width = 20 μs)

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 2 Adc, I <sub>B1</sub> = 0.4 Adc I <sub>B2</sub> = 1 Adc V <sub>CC</sub> = 300 Vdc	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	90 105	150 –	ns
t <sub>off</sub>	Turn-off Time		@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	1.15 1.5	1.3 –	μs
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 2 Adc, I <sub>B1</sub> = 0.4 Adc I <sub>B2</sub> = 0.4 Adc V <sub>CC</sub> = 300 Vdc	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	90 110	150 –	ns
t <sub>off</sub>	Turn-off Time		@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	2.1 –	– 3.1	2.4 –	μs

### SWITCHING CHARACTERISTICS: Inductive Load (V<sub>clamp</sub> = 300 V, V<sub>CC</sub> = 15 V, L = 200 μH)

t <sub>f</sub>	Fall Time	I <sub>C</sub> = 1 Adc I <sub>B1</sub> = 100 mA I <sub>B2</sub> = 500 mA	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	90 93	150 –	ns
t <sub>s</sub>	Storage Time		@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	0.72 1.05	0.9 –	μs
t <sub>c</sub>	Crossover Time		@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	95 95	150 –	ns
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 2 Adc I <sub>B1</sub> = 0.4 Adc I <sub>B2</sub> = 0.4 Adc	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	80 105	150 –	ns
t <sub>s</sub>	Storage Time		@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	1.95 –	– 2.9	2.25 –	μs
t <sub>c</sub>	Crossover Time		@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	– –	225 450	300 –	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL STATIC CHARACTERISTICS

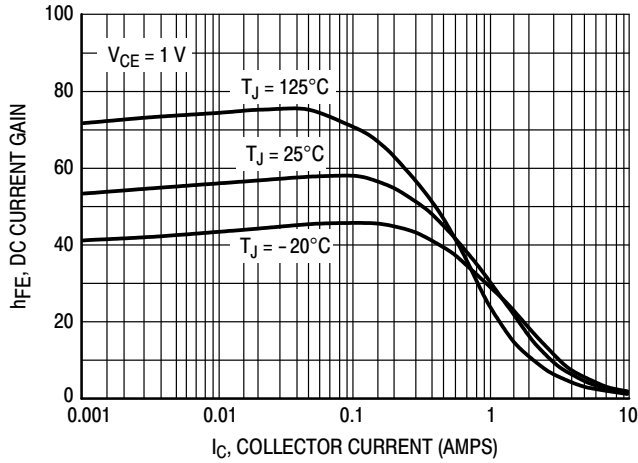


Figure 1. DC Current Gain @ 1 Volt

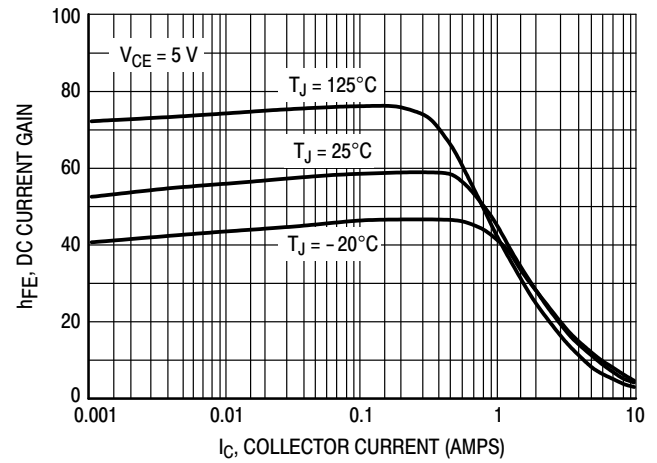


Figure 2. DC Current Gain @ 5 Volt

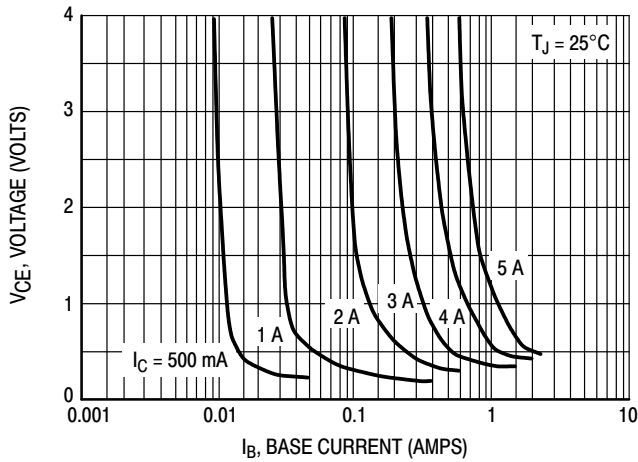


Figure 3. Collector Saturation Region

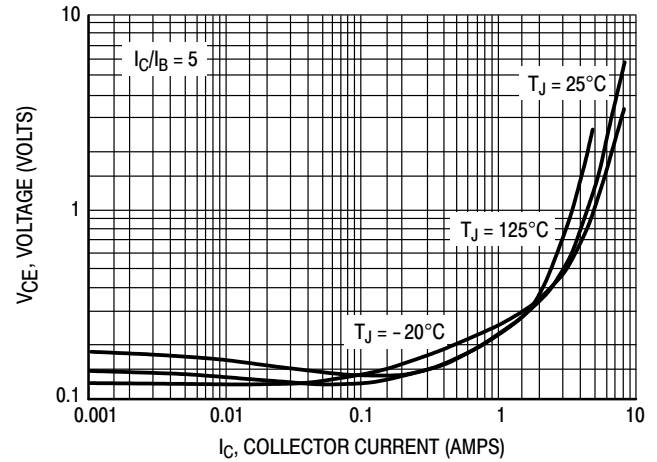


Figure 4. Collector-Emitter Saturation Voltage

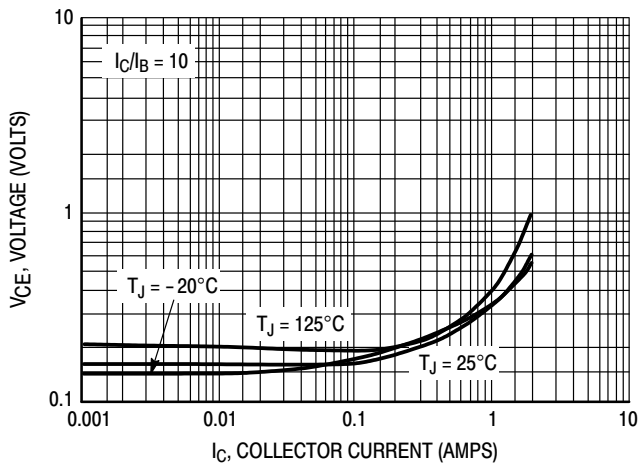


Figure 5. Collector-Emitter Saturation Voltage

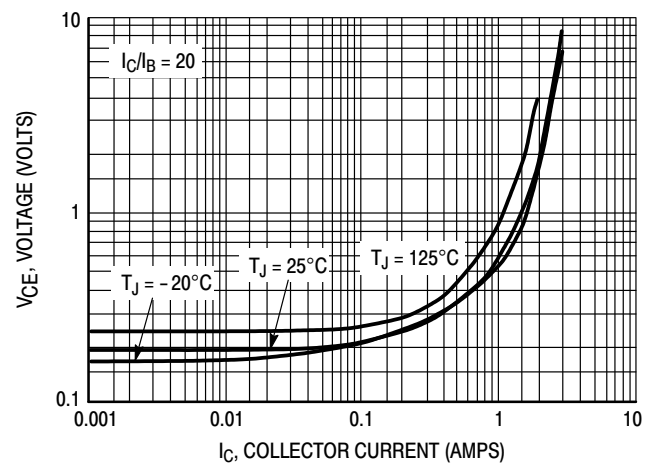


Figure 6. Collector-Emitter Saturation Voltage

TYPICAL STATIC CHARACTERISTICS (continue)

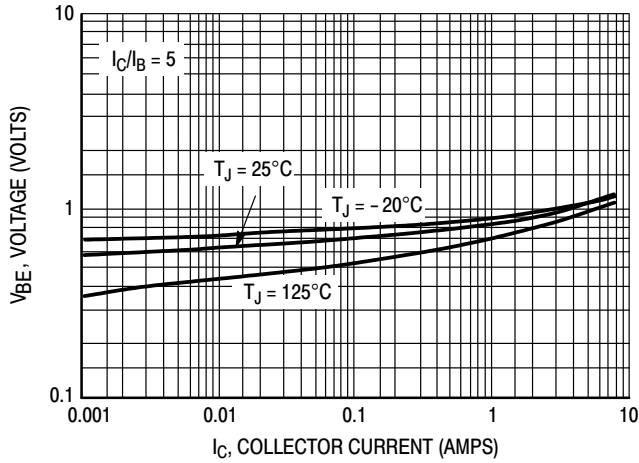


Figure 7. Base-Emitter Saturation Region

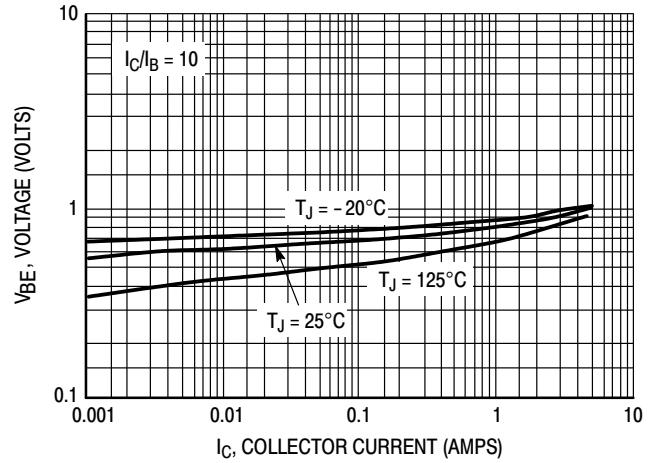


Figure 8. Base-Emitter Saturation Region

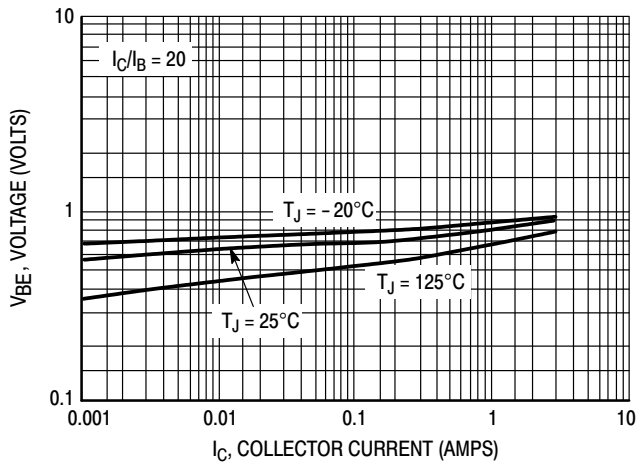


Figure 9. Base-Emitter Saturation Region

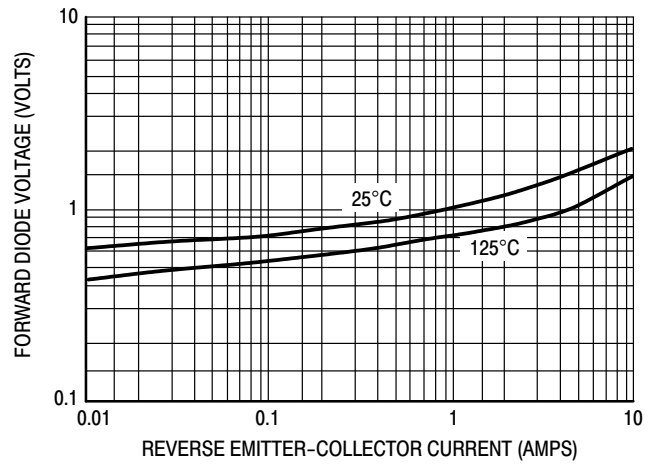


Figure 10. Forward Diode Voltage

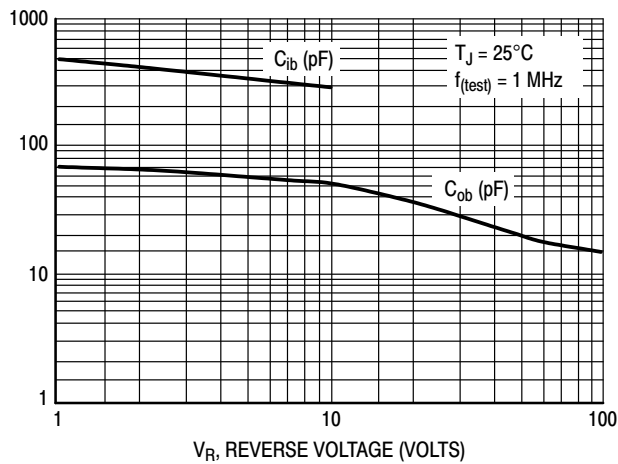


Figure 11. Capacitance

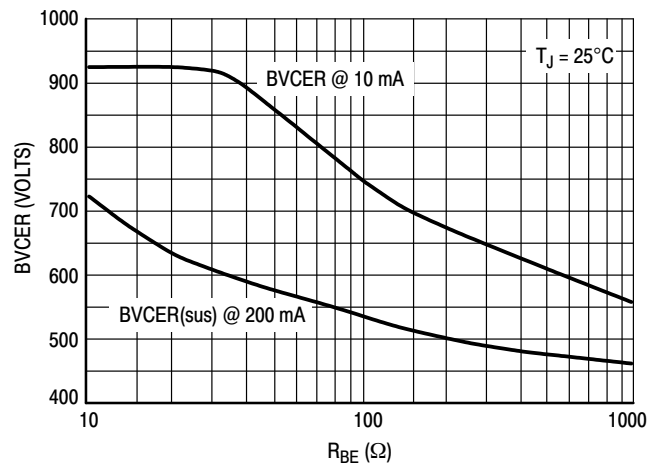


Figure 12.  $BVCER = f(I_{CER})$

TYPICAL SWITCHING CHARACTERISTICS

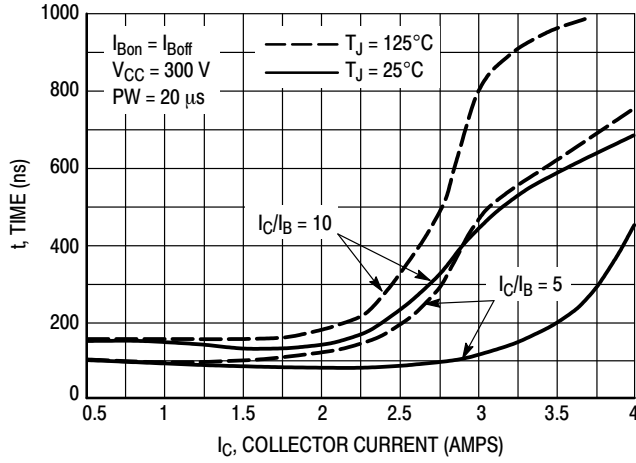


Figure 13. Resistive Switch Time,  $t_{on}$

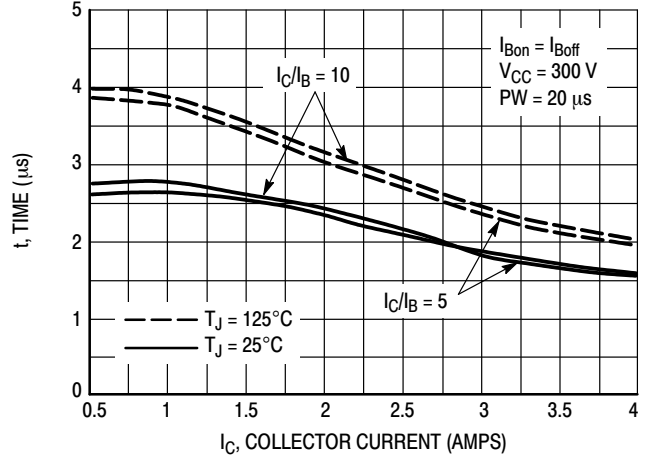


Figure 14. Resistive Switch Time,  $t_{off}$

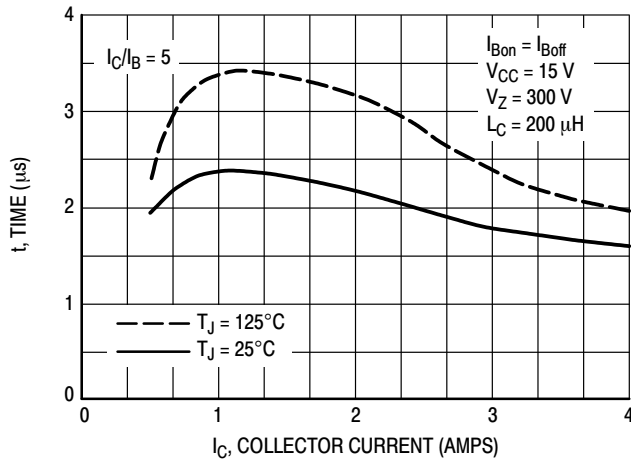


Figure 15. Inductive Storage Time,  $t_{si}$  @  $I_C/I_B = 5$

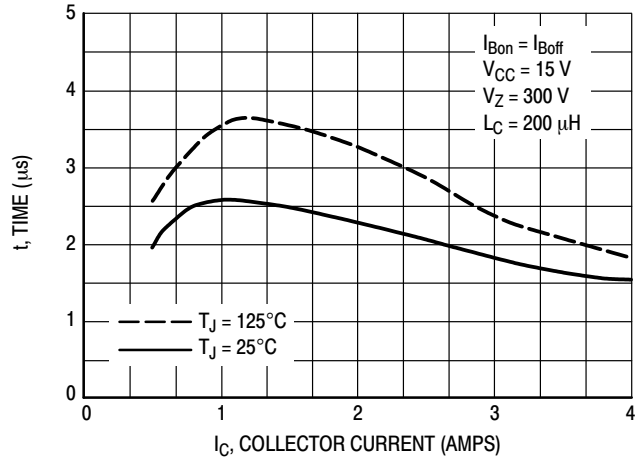


Figure 16. Inductive Storage Time,  $t_{si}$  @  $I_C/I_B = 10$

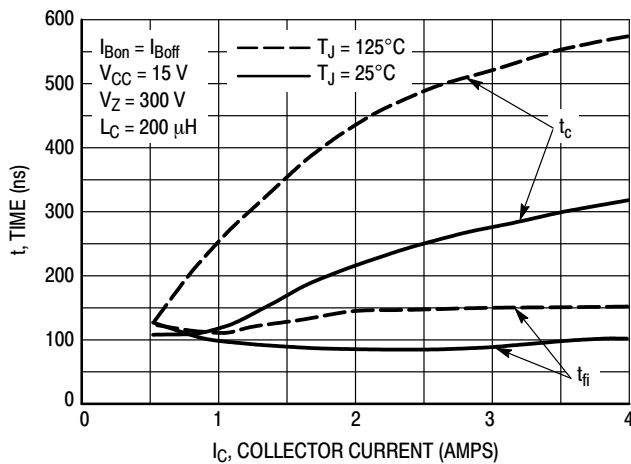


Figure 17. Inductive Switching,  $t_c$  &  $t_{fi}$  @  $I_C/I_B = 5$

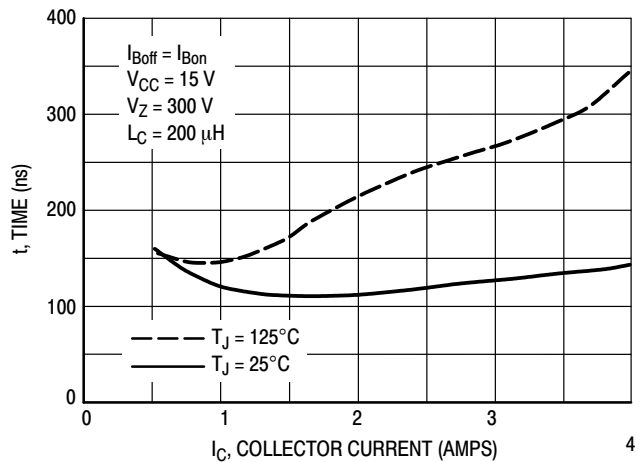


Figure 18. Inductive Switching,  $t_{fi}$  @  $I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS (continue)

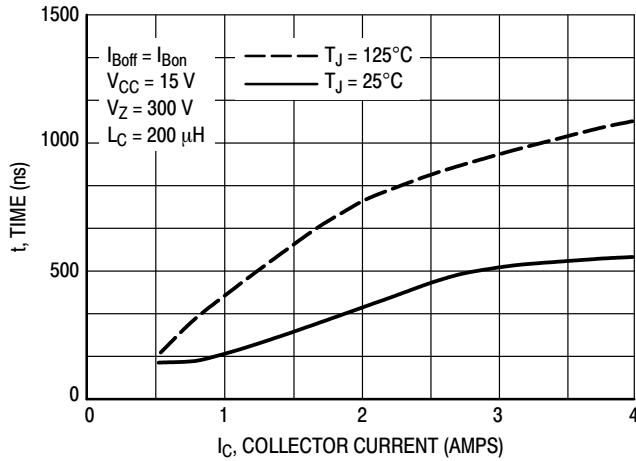


Figure 19. Inductive Switching,  $t_c$  @  $I_C/I_B = 10$

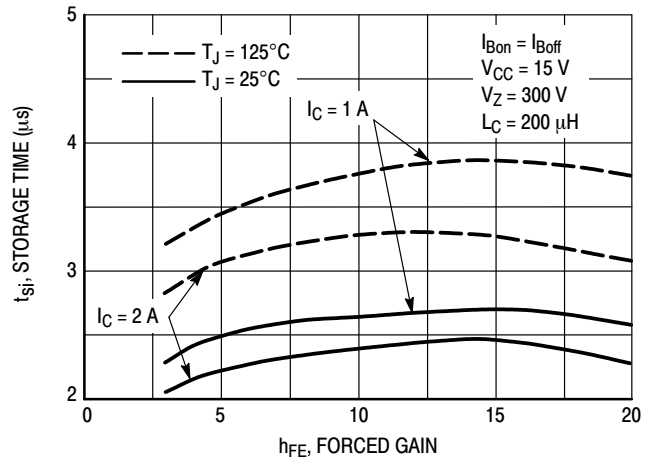


Figure 20. Inductive Storage Time

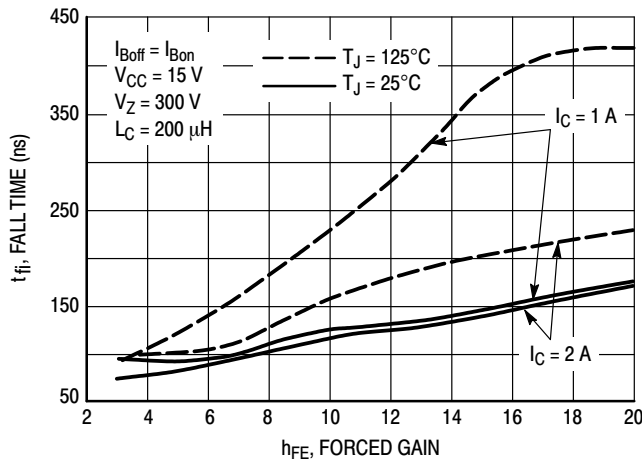


Figure 21. Inductive Fall Time

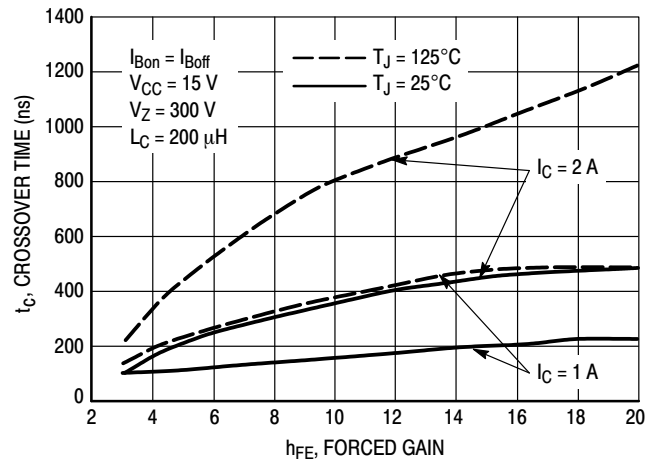


Figure 22. Inductive Crossover Time

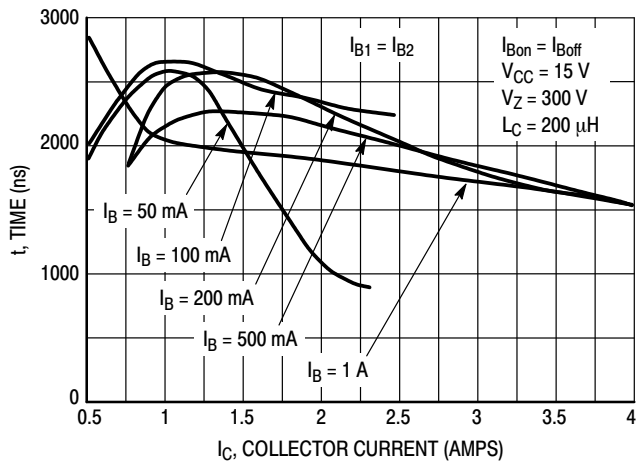


Figure 23. Inductive Storage Time,  $t_{si}$

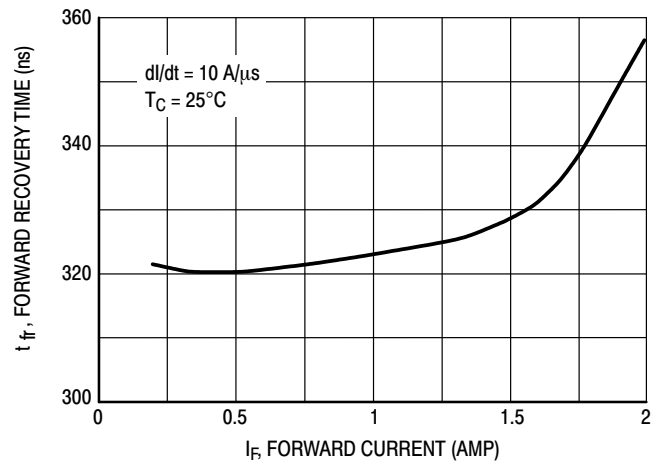
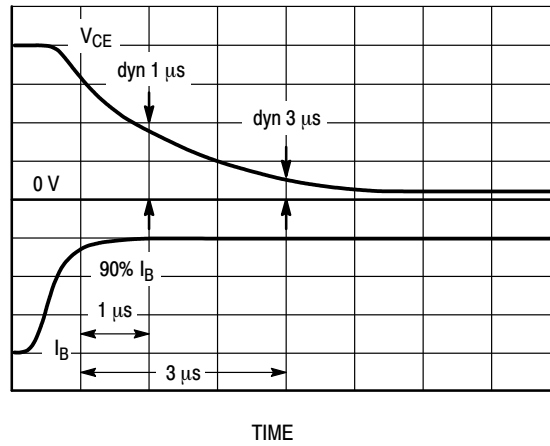


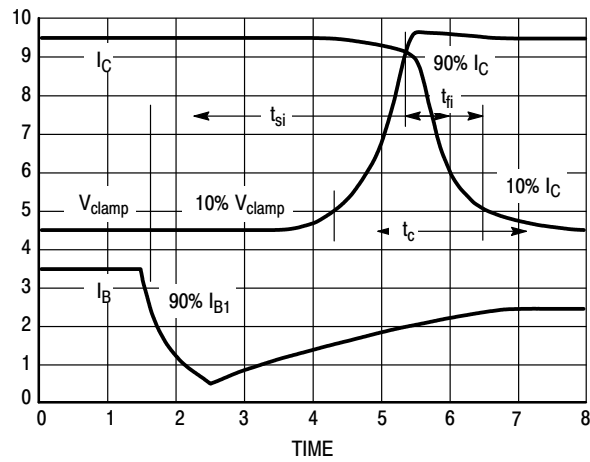
Figure 24. Forward Recovery Time  $t_{fr}$

# BUL45D2G

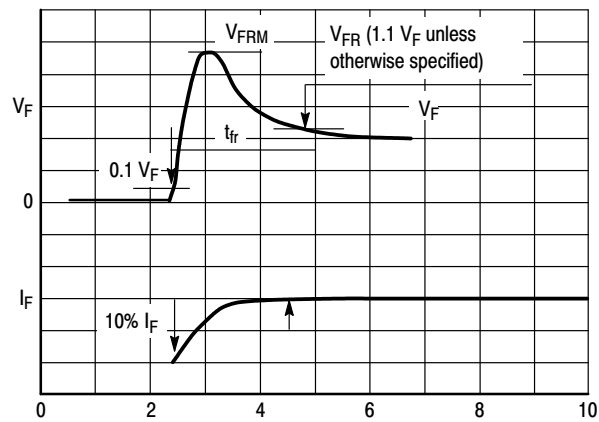
## TYPICAL SWITCHING CHARACTERISTICS (continue)



**Figure 25. Dynamic Saturation Voltage Measurements**



**Figure 26. Inductive Switching Measurements**

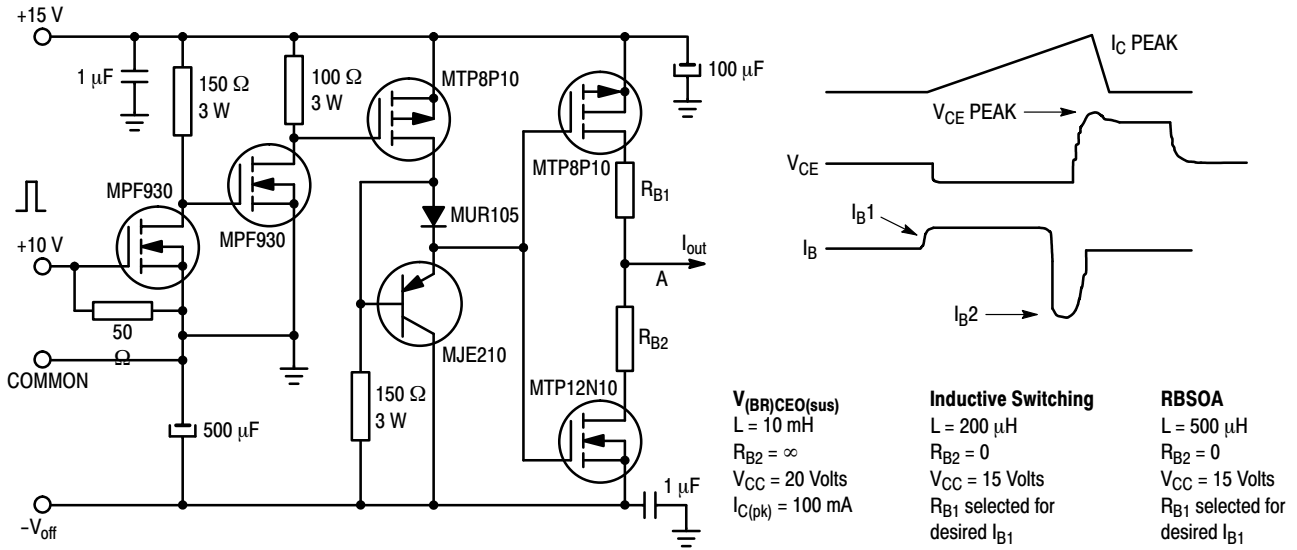


**Figure 27.  $t_{fr}$  Measurements**



TYPICAL SWITCHING CHARACTERISTICS (continue)

Table 1. Inductive Load Switching Drive Circuit



TYPICAL CHARACTERISTICS

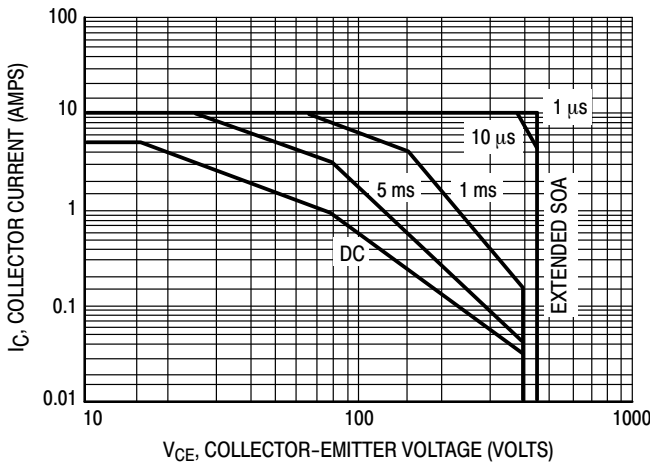


Figure 28. Forward Bias Safe Operating Area

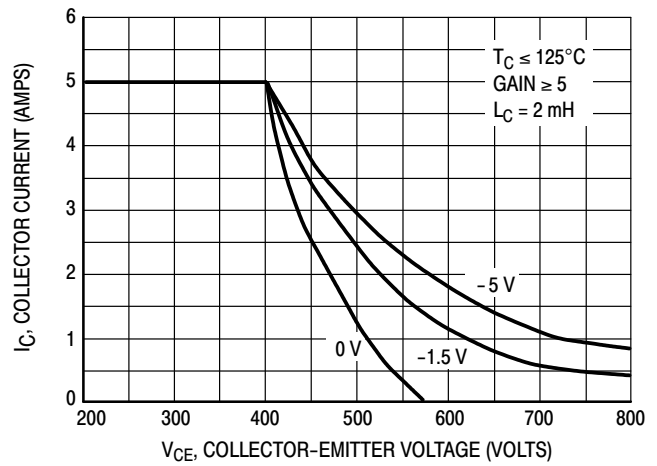


Figure 29. Reverse Bias Safe Operating Area

# BUL45D2G

## TYPICAL CHARACTERISTICS (continue)

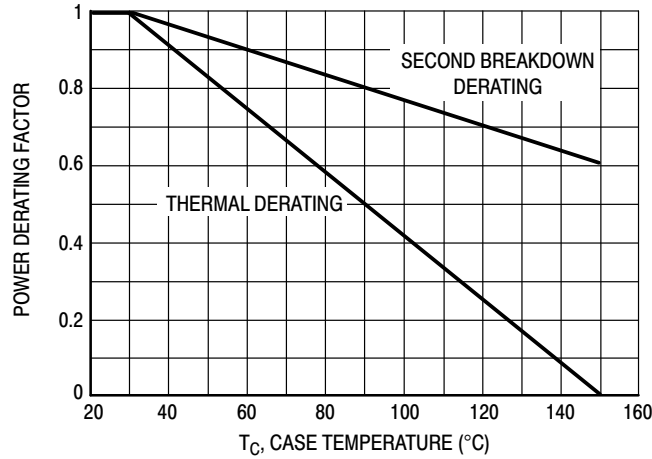


Figure 30. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C-V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 28 is based on  $T_C = 25^\circ\text{C}$ ;  $T_{J(pk)}$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when  $T_C > 25^\circ\text{C}$ . Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on

Figure 28 may be found at any case temperature by using the appropriate curve on Figure 30.

$T_{J(pk)}$  may be calculated from the data in Figure 31. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base to emitter junction reverse biased. The safe level is specified as a reverse biased safe operating area (Figure 29). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

## TYPICAL THERMAL RESPONSE

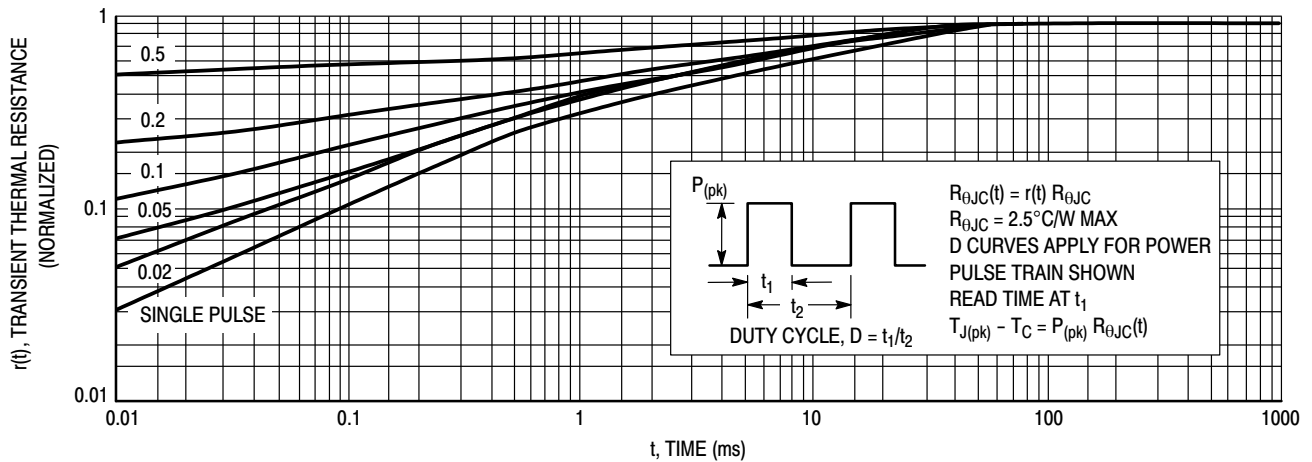


Figure 31. Typical Thermal Response ( $Z_{\theta JC}(t)$ ) for BUL45D2

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